I-V and C-V characterization of semiconductor thin flms

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ABSTRACT

Cuprous oxide (Cu2O) and ZnSe thin films were potentiostatically electrodeposited on indium-doped tin oxide (ITO) substrates in order to investigate the I-V and C-V characteristics of ITO/n-Cu₂O/(p-Cu_xS or metal or electrolyte) and ITO/p-ZnSe/electrolyte systems. An electrochemical cell containing aqueous solutions of 0-1 M sodium acetate and 1.6x10⁻² M cupric acetate was used for electro deposition of Cu₂O thin films on ITO-coated glass substrates. Potentiostatic condition of -250 mV against standard calomel electrodes (SEC) was used for the electro deposition. To convert the top layers of the Cu2O to CuxS by sulphidation, exposed the surface to a spray of aqueous solution of sodium sulphide or to a mixture of hydrogen sulphide and nitrogen gases to foam ITO/n-Cu2O/p-CuxS system. For the system ITO/n-Cu₂O/metal, metal layer was evaporated on to the n-Cu₂O surface. An electrolyte of 0.1 M sodium acetate was used in the ITO/n-Cu₂O/electrolyte system. Electro deposition of ZnSe thin films were carried out under potentionstatic condition at -550 mV against SCE using aqueous solutions of 0.1 M ZnSO₄ and 10⁻⁵ M SeO₂ at the temperature of 65° C. The theoretical and experimental I-V characteristics of ITO/n-Cu₂O/(p-Cu_xS or metal or electrolyte) system suggest that Cu₂O films made on ITO substrate form Schottky type junctions at the back contact in addition to the Cu₂O/(p-Cu_xS of metal or electrolyte) junctions. Furthermore, C-V characteristics suggest that the doping concentration of the Cu₂O layer is in the order of 10¹⁸. Light and dark I-V measurements of doped and undoped ITO/ZnSe in KI electrolyte suggest the p-type photoconductivity in this system and C-V measurements confirmed it.

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